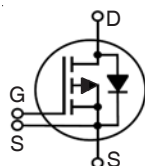


PolarP™ Power MOSFET

IXTN170P10P

$$\begin{aligned} V_{DSS} &= -100V \\ I_{D25} &= -170A \\ R_{DS(on)} &\leq 14m\Omega \end{aligned}$$

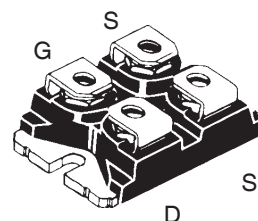
P-Channel Enhancement Mode
Avalanche Rated



miniBLOC, SOT-227
E153432



Symbol	Test Conditions	Maximum Ratings	
V_{DSS}	$T_J = 25^\circ\text{C}$ to 150°C	-100	V
V_{DGR}	$T_J = 25^\circ\text{C}$ to 150°C , $R_{GS} = 1M\Omega$	-100	V
V_{GSS}	Continuous	± 20	V
V_{GSM}	Transient	± 30	V
I_{D25}	$T_C = 25^\circ\text{C}$	-170	A
I_{DM}	$T_C = 25^\circ\text{C}$, Pulse Width Limited by T_{JM}	- 510	A
I_A	$T_C = 25^\circ\text{C}$	-170	A
E_{AS}	$T_C = 25^\circ\text{C}$	3.5	J
dv/dt	$I_S \leq I_{DM}$, $V_{DD} \leq V_{DSS}$, $T_J \leq 150^\circ\text{C}$	10	V/ns
P_D	$T_C = 25^\circ\text{C}$	890	W
T_J		-55 ... +150	$^\circ\text{C}$
T_{JM}		150	$^\circ\text{C}$
T_{stg}		-55 ... +150	$^\circ\text{C}$
V_{ISOL}	50/60 Hz, RMS	t = 1 minute	2500 V~
	$I_{ISOL} \leq 1\text{mA}$	t = 1 second	3000 V~
M_d	Mounting Torque	1.5/13	Nm/lb.in.
	Terminal Connection Torque	1.3/11.5	Nm/lb.in.
Weight		30	g



G = Gate D = Drain
S = Source

Either Source Terminal at miniBLOC can be used as Main or Kelvin Source.

Features

- International Standard Package
- miniBLOC, with Aluminium Nitride Isolation
- Rugged PolarP™ Process
- High Current Handling Capability
- Fast Intrinsic Diode
- Avalanche Rated
- Low Package Inductance

Advantages

- Easy to Mount
- Space Savings
- High Power Density

Applications

- High-Side Switches
- Push Pull Amplifiers
- DC Choppers
- Automatic Test Equipment
- Current Regulators

Symbol	Test Conditions ($T_J = 25^\circ\text{C}$, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
BV_{DSS}	$V_{GS} = 0V$, $I_D = -250\mu\text{A}$	-100		V
$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -1\text{mA}$	- 2.0		V
I_{GSS}	$V_{GS} = \pm 20V$, $V_{DS} = 0V$			± 100 nA
I_{DSS}	$V_{DS} = V_{DSS}$, $V_{GS} = 0V$ $T_J = 125^\circ\text{C}$			- 50 μA
				- 250 μA
$R_{DS(on)}$	$V_{GS} = -10V$, $I_D = 0.5 \cdot I_{D25}$, Note 1			14 m Ω

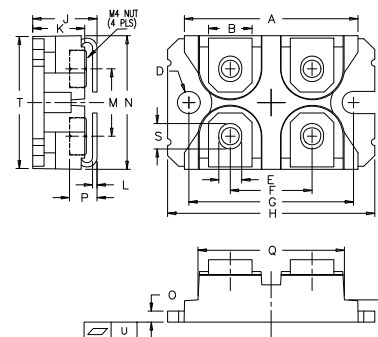
Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
g_{fs}	V _{DS} = -10V, I _D = 0.5 • I _{D25} , Note 1	35	58	S
C_{iss}	V _{GS} = 0V, V _{DS} = -25V, f = 1MHz		12.6	nF
C_{oss}			4190	pF
C_{rss}			930	pF
t_{d(on)}	Resistive Switching Times V _{GS} = -10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25} R _G = 1Ω (External)		32	ns
t_r			75	ns
t_{d(off)}			82	ns
t_f			45	ns
Q_{g(on)}	V _{GS} = -10V, V _{DS} = 0.5 • V _{DSS} , I _D = 0.5 • I _{D25}		240	nC
Q_{gs}			45	nC
Q_{gd}			120	nC
R_{thJC}		0.05		0.14 °C/W
R_{thCS}				°C/W

Source-Drain Diode

Symbol	Test Conditions (T _J = 25°C, Unless Otherwise Specified)	Characteristic Values		
		Min.	Typ.	Max.
I_S	V _{GS} = 0V			-170 A
I_{SM}	Repetitive, Pulse Width Limited by T _{JM}			- 680 A
V_{SD}	I _F = - 85A, V _{GS} = 0V, Note 1			- 3.3 V
t_{rr}	I _F = - 85A, -di/dt = -100A/μs V _R = - 50V, V _{GS} = 0V		176	ns
Q_{RM}			1.25	μC
I_{RM}			-14.2	A

Note 1: Pulse test, t ≤ 300μs, duty cycle, d ≤ 2%.

SOT-227B (IXTN) Outline



(M4 screws (4x) supplied)

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.240	1.255	31.50	31.88
B	.307	.323	7.80	8.20
C	.161	.169	4.09	4.29
D	.161	.169	4.09	4.29
E	.161	.169	4.09	4.29
F	.587	.595	14.91	15.11
G	1.186	1.193	30.12	30.30
H	1.496	1.505	38.00	38.23
J	.460	.481	11.68	12.22
K	.351	.378	8.92	9.60
L	.030	.033	0.76	0.84
M	.496	.506	12.60	12.85
N	.990	1.001	25.15	25.42
O	.078	.084	1.98	2.13
P	.195	.235	4.95	5.97
Q	1.045	1.059	26.54	26.90
R	.155	.174	3.94	4.42
S	.186	.191	4.72	4.85
T	.968	.987	24.59	25.07
U	-.002	.004	-0.05	0.1

IXYS Reserves the Right to Change Limits, Test Conditions, and Dimensions.

IXYS MOSFETs and IGBTs are covered by one or more of the following U.S. patents:	4,835,592	4,931,844	5,049,961	5,237,481	6,162,665	6,404,065 B1	6,683,344	6,727,585	7,005,734 B2	7,157,338B2
	4,860,072	5,017,508	5,063,307	5,381,025	6,259,123 B1	6,534,343	6,710,405 B2	6,759,692	7,063,975 B2	
	4,881,106	5,034,796	5,187,117	5,486,715	6,306,728 B1	6,583,505	6,710,463	6,771,478 B2	7,071,537	

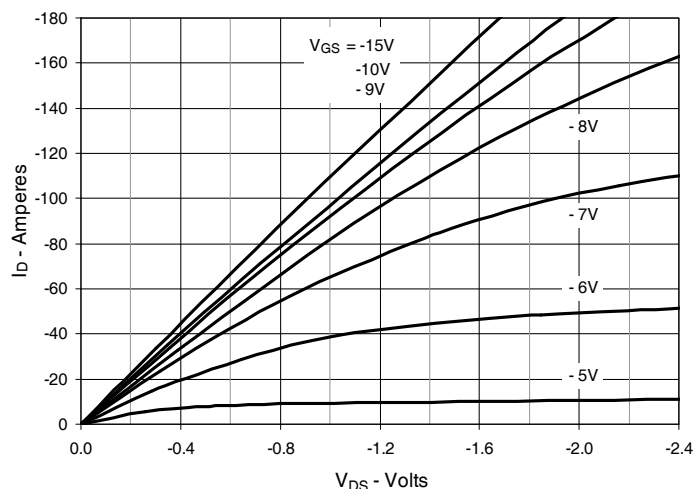
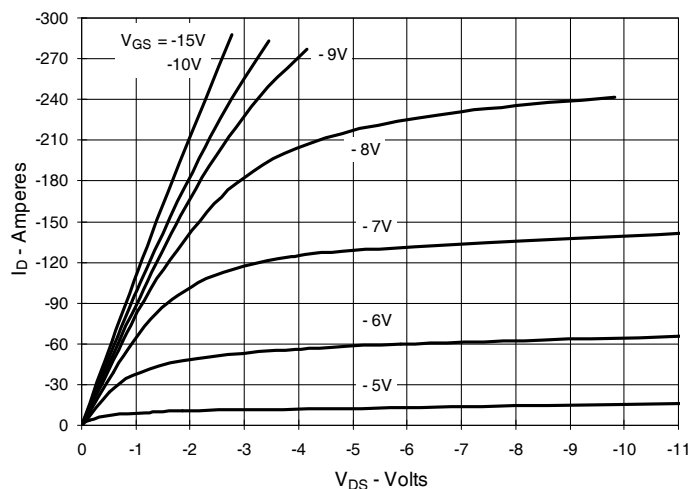
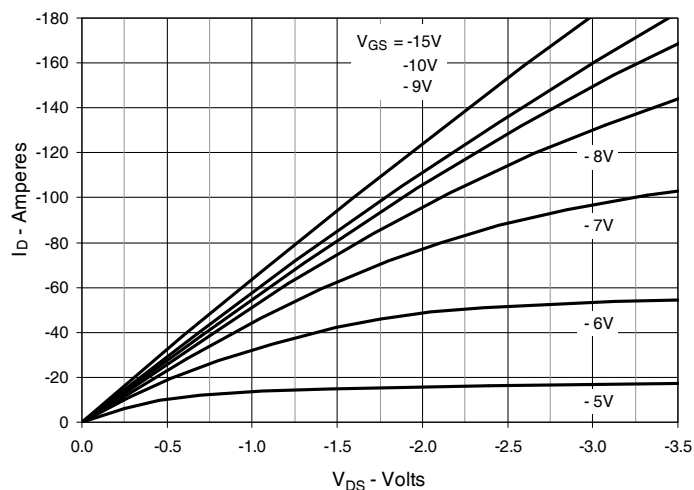
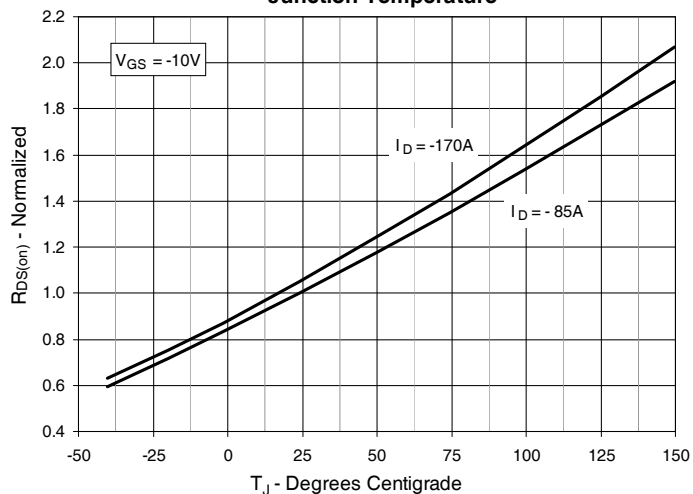
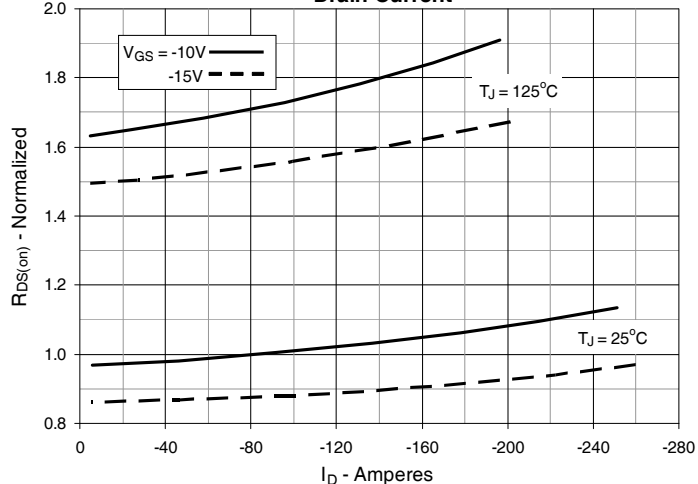
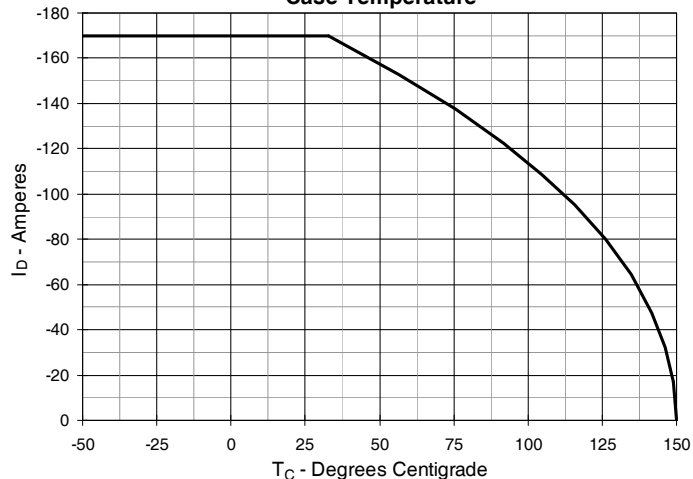
Fig. 1. Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 2. Extended Output Characteristics @ $T_J = 25^\circ\text{C}$

Fig. 3. Output Characteristics @ $T_J = 125^\circ\text{C}$

Fig. 4. $R_{DS(on)}$ Normalized to $I_D = -85\text{A}$ Value vs. Junction Temperature

Fig. 5. $R_{DS(on)}$ Normalized to $I_D = -85\text{A}$ Value vs. Drain Current

Fig. 6. Maximum Drain Current vs. Case Temperature


Fig. 7. Input Admittance

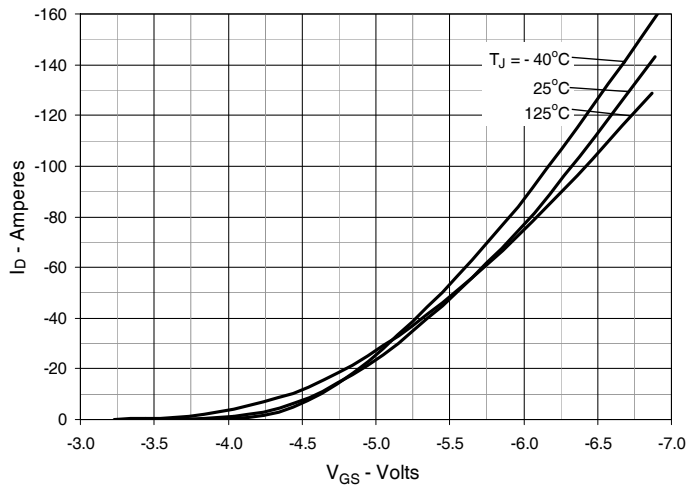


Fig. 8. Transconductance

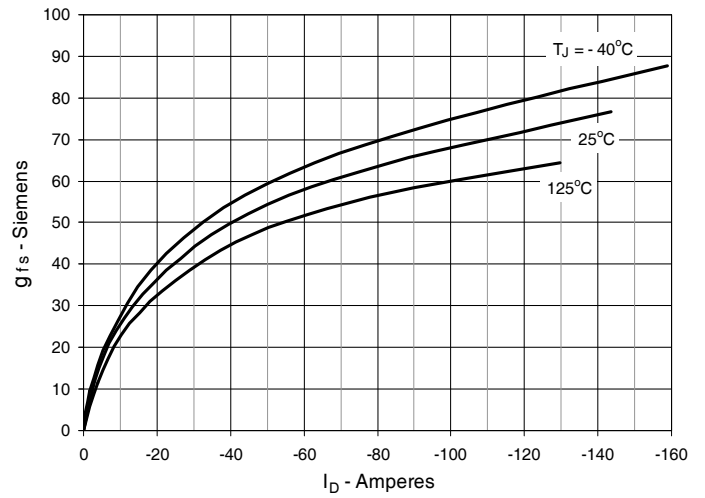


Fig. 9. Forward Voltage Drop of Intrinsic Diode

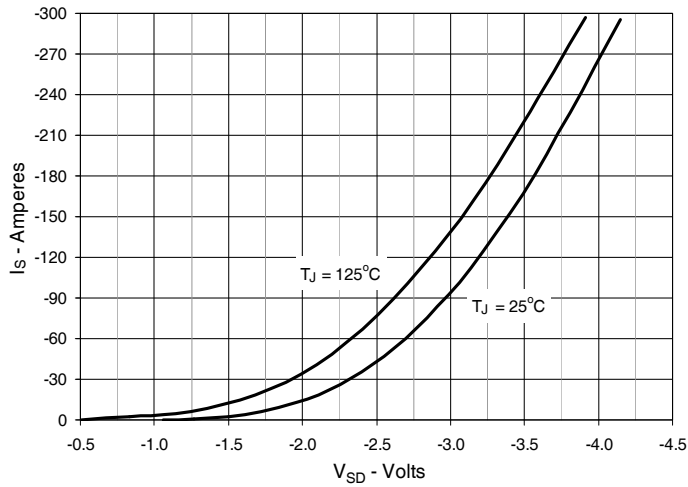


Fig. 10. Gate Charge

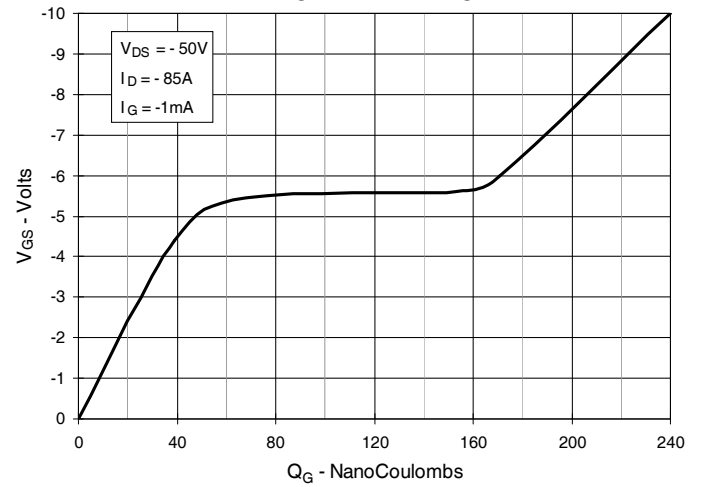


Fig. 11. Capacitance

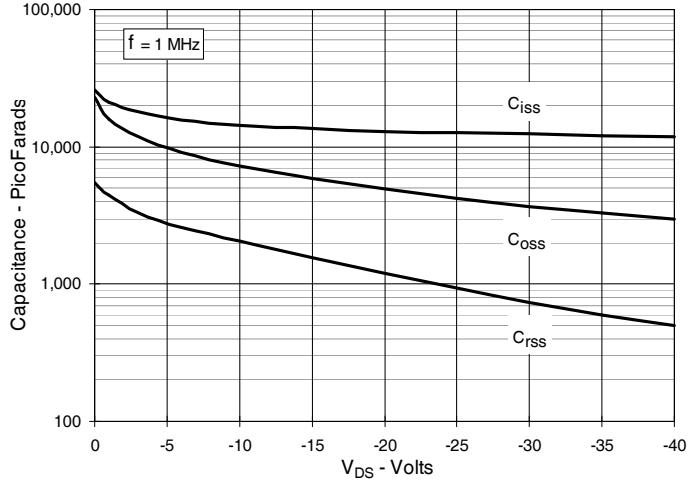


Fig. 12. Forward-Bias Safe Operating Area

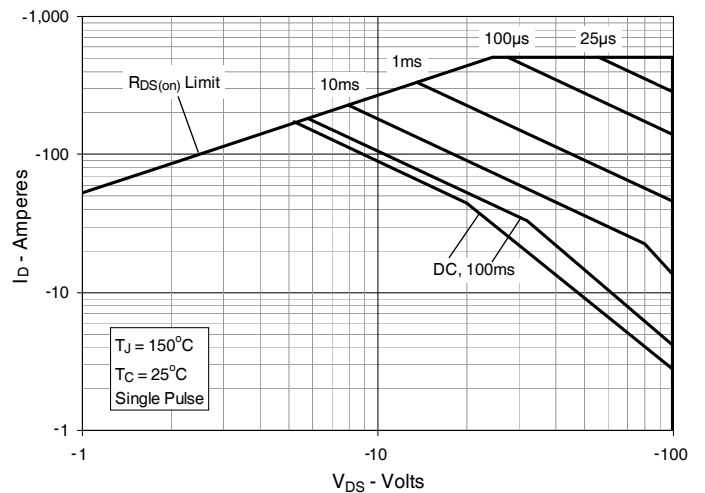
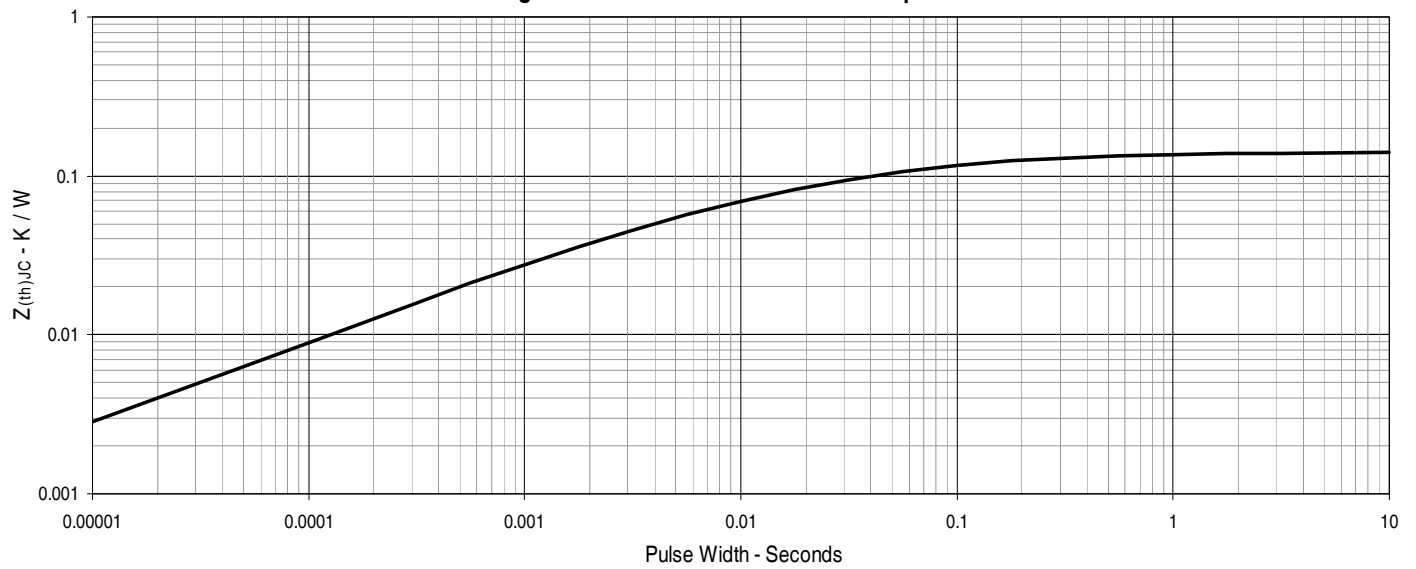


Fig. 13. Maximum Transient Thermal Impedance





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